



NPN SILICON GERMANIUM RF TRANSISTOR

NESG2031M16

NPN SiGe RF TRANSISTOR FOR LOW NOISE, HIGH-GAIN AMPLIFICATION 6-PIN LEAD-LESS MINIMOLD (M16, 1208 PKG)

FEATURES

- The device is an ideal choice for low noise, high-gain amplification
 - NF = 0.8 dB TYP., $G_a = 17.0$ dB TYP. @ $V_{CE} = 2$ V, $I_c = 5$ mA, $f = 2$ GHz
 - NF = 1.3 dB TYP., $G_a = 10.0$ dB TYP. @ $V_{CE} = 2$ V, $I_c = 5$ mA, $f = 5.2$ GHz
- Maximum stable power gain: MSG = 21.5 dB TYP. @ $V_{CE} = 3$ V, $I_c = 20$ mA, $f = 2$ GHz
- High breakdown voltage technology for SiGe Tr. adopted: V_{CEO} (absolute maximum ratings) = 5.0 V
- 6-pin lead-less minimold (M16, 1208 PKG)

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ORDERING INFORMATION

Part Number	Order Number	Package	Quantity	Supplying Form
NESG2031M16	NESG2031M16-A	6-pin lead-less minimold (M16, 1208 PKG) (Pb-Free)	50 pcs (Non reel)	<ul style="list-style-type: none"> 8 mm wide embossed taping Pin 1 (Collector), Pin 6 (Emitter) face the perforation side of the tape
NESG2031M16-T3	NESG2031M16-T3-A		10 kpcs/reel	

Remark To order evaluation samples, please contact your nearby sales office.
Unit sample quantity is 50 pcs.

ABSOLUTE MAXIMUM RATINGS ($T_A = +25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V_{CBO}	13.0	V
Collector to Emitter Voltage	V_{CEO}	5.0	V
Emitter to Base Voltage	V_{EBO}	1.5	V
Collector Current	I_c	35	mA
Total Power Dissipation	P_{tot} ^{Note}	175	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to +150	$^\circ\text{C}$

Note Mounted on $1.08 \text{ cm}^2 \times 1.0 \text{ mm}$ (t) glass epoxy PCB

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

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ELECTRICAL CHARACTERISTICS (T_A = +25°C)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
DC Characteristics						
Collector Cut-off Current	I _{CBO}	V _{CB} = 5 V, I _E = 0 mA	–	–	100	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} = 1 V, I _C = 0 mA	–	–	100	nA
DC Current Gain	h _{FE} ^{Note 1}	V _{CE} = 2 V, I _C = 5 mA	130	190	260	–
RF Characteristics						
Gain Bandwidth Product	f _T	V _{CE} = 3 V, I _C = 20 mA, f = 2 GHz	20	25	–	GHz
Insertion Power Gain	S _{21e} ²	V _{CE} = 3 V, I _C = 20 mA, f = 2 GHz	16.0	18.0	–	dB
Noise Figure (1)	NF	V _{CE} = 2 V, I _C = 5 mA, f = 2 GHz, Z _S = Z _{Sopt} , Z _L = Z _{Lopt}	–	0.8	1.1	dB
Noise Figure (2)	NF	V _{CE} = 2 V, I _C = 5 mA, f = 5.2 GHz, Z _S = Z _{Sopt} , Z _L = Z _{Lopt}	–	1.3	–	dB
Associated Gain (1)	G _a	V _{CE} = 2 V, I _C = 5 mA, f = 2 GHz, Z _S = Z _{Sopt} , Z _L = Z _{Lopt}	15.0	17.0	–	dB
Associated Gain (2)	G _a	V _{CE} = 2 V, I _C = 5 mA, f = 5.2 GHz, Z _S = Z _{Sopt} , Z _L = Z _{Lopt}	–	10.0	–	dB
Reverse Transfer Capacitance	C _{re} ^{Note 2}	V _{CB} = 2 V, I _E = 0 mA, f = 1 MHz	–	0.15	0.25	pF
Maximum Stable Power Gain	MSG ^{Note 3}	V _{CE} = 3 V, I _C = 20 mA, f = 2 GHz	19.0	21.5	–	dB
Gain 1 dB Compression Output Power	P _{O(1 dB)}	V _{CE} = 3 V, I _{C(set)} = 20 mA (RF OFF), f = 2 GHz, Z _S = Z _{Sopt} , Z _L = Z _{Lopt}	–	13	–	dBm
Output 3rd Order Intercept Point	OIP ₃	V _{CE} = 3 V, I _{C(set)} = 20 mA (RF OFF), f = 2 GHz, Z _S = Z _{Sopt} , Z _L = Z _{Lopt}	–	23	–	dBm

Notes 1. Pulse measurement: PW ≤ 350 μs, Duty Cycle ≤ 2%

2. Collector to base capacitance when the emitter grounded

$$3. \text{MSG} = \left| \frac{S_{21}}{S_{12}} \right|$$

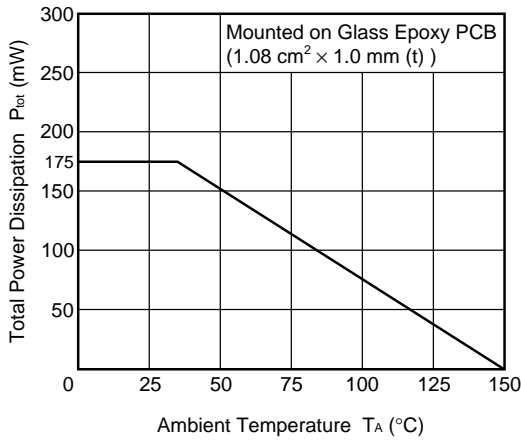
h_{FE} CLASSIFICATION

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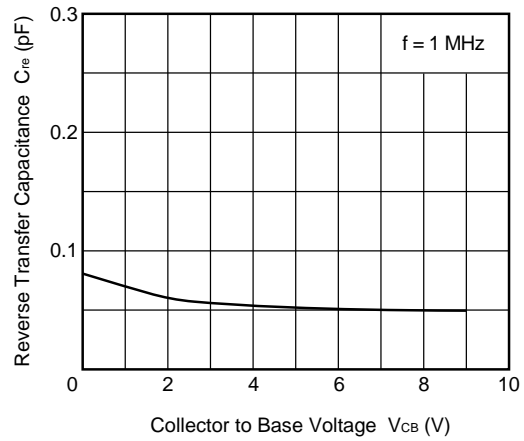
Rank	FB/YFB
Marking	zF
h _{FE} Value	130 to 260

<R> TYPICAL CHARACTERISTICS (T_A = +25°C, unless otherwise specified)

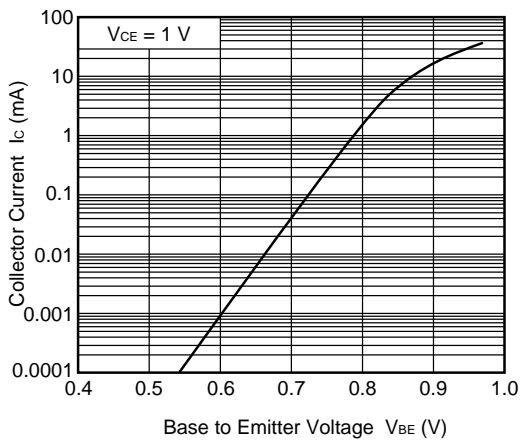
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



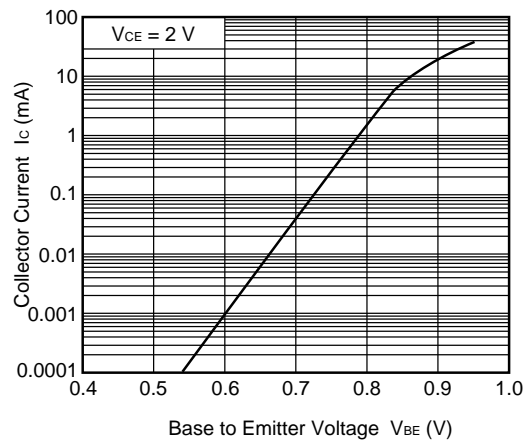
REVERSE TRANSFER CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE



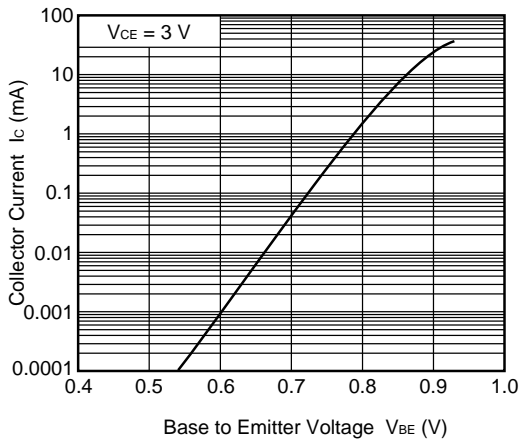
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



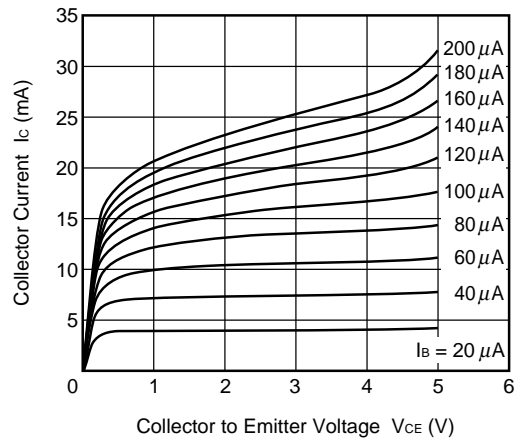
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE

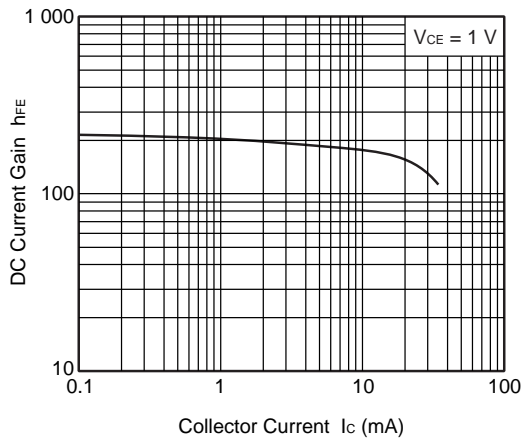


COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE

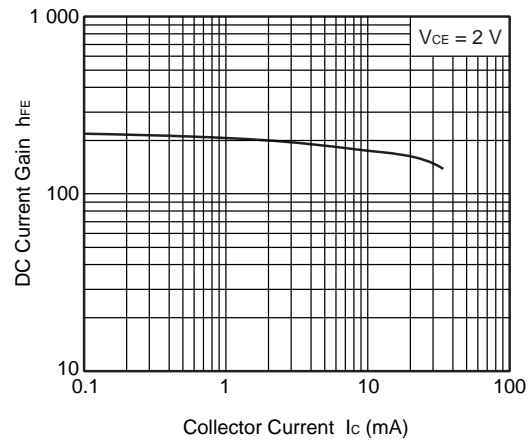


Remark The graphs indicate nominal characteristics.

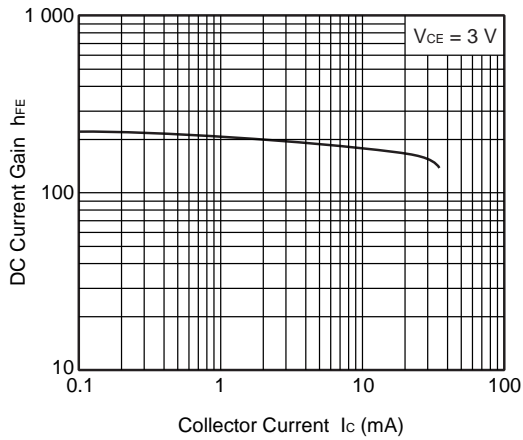
DC CURRENT GAIN vs.
COLLECTOR CURRENT



DC CURRENT GAIN vs.
COLLECTOR CURRENT

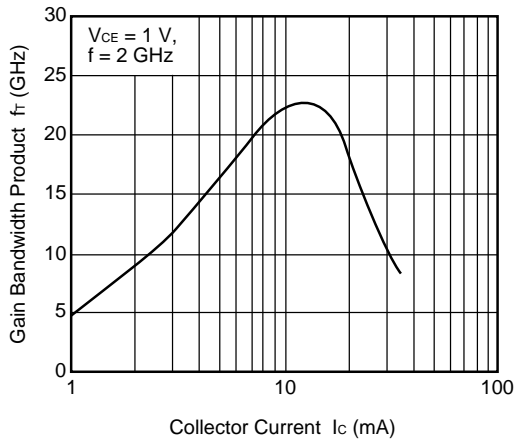


DC CURRENT GAIN vs.
COLLECTOR CURRENT

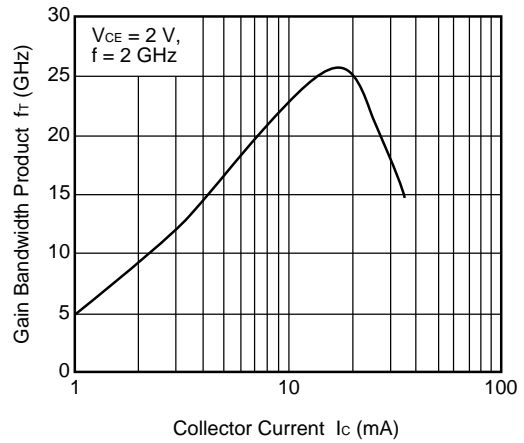


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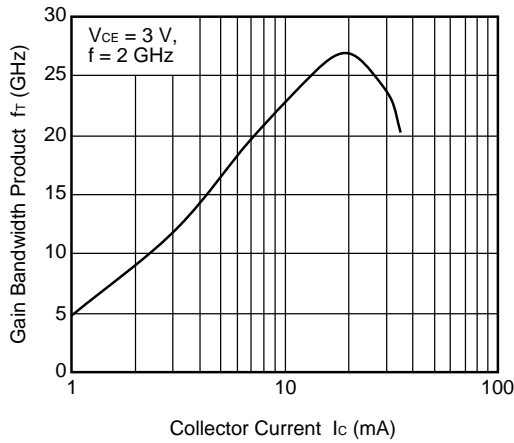
GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT



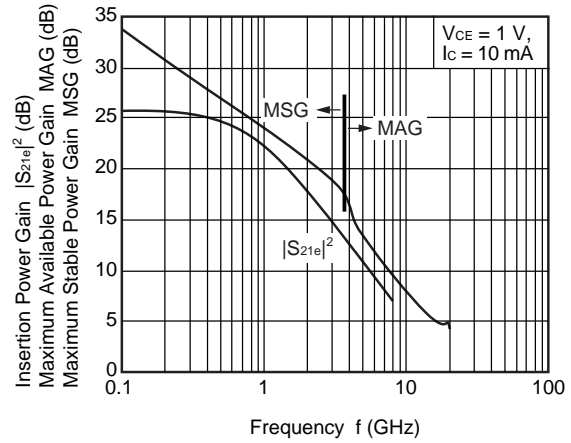
GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT



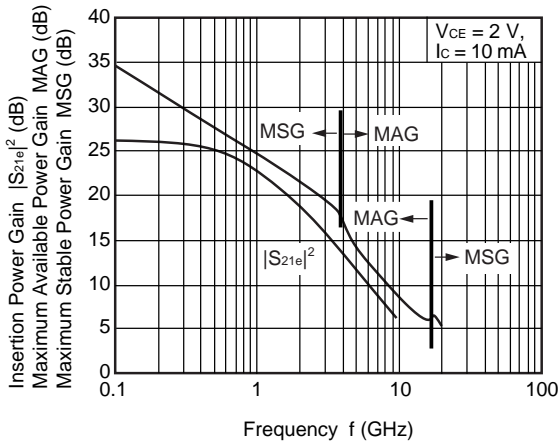
GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT



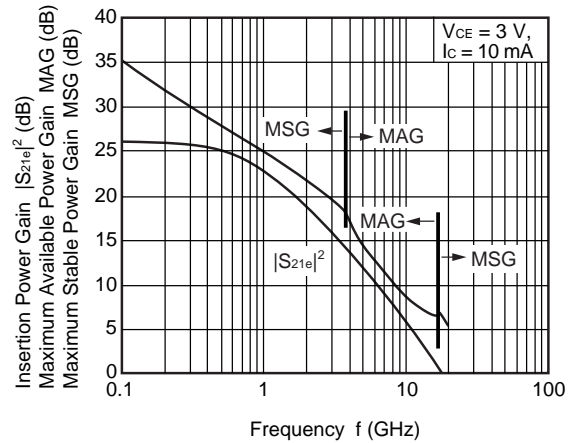
INSERTION POWER GAIN, MAG, MSG vs. FREQUENCY



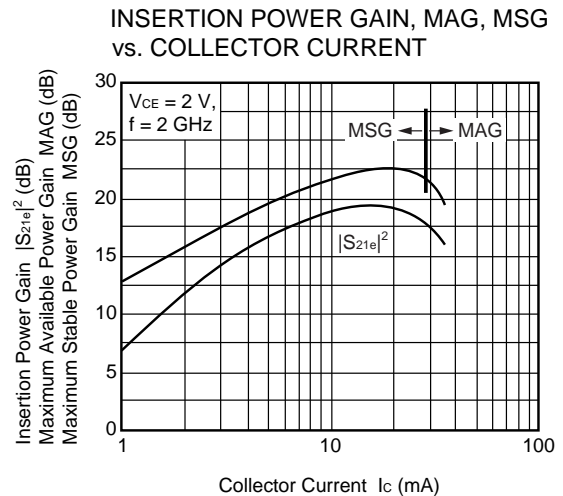
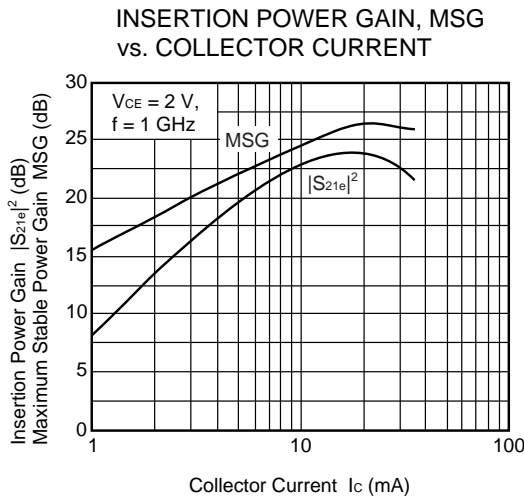
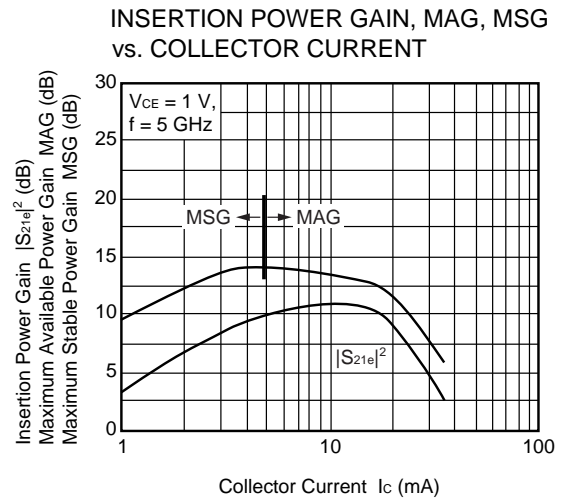
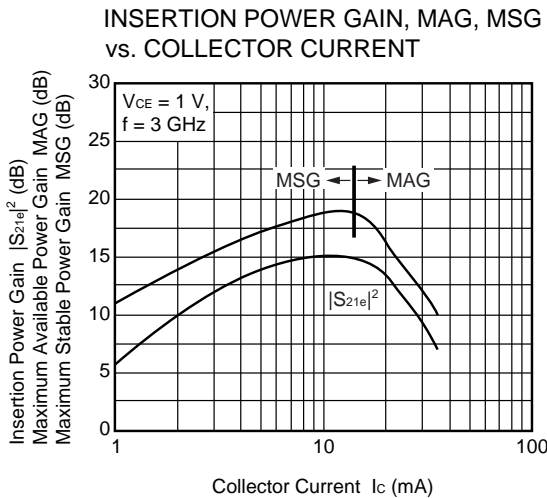
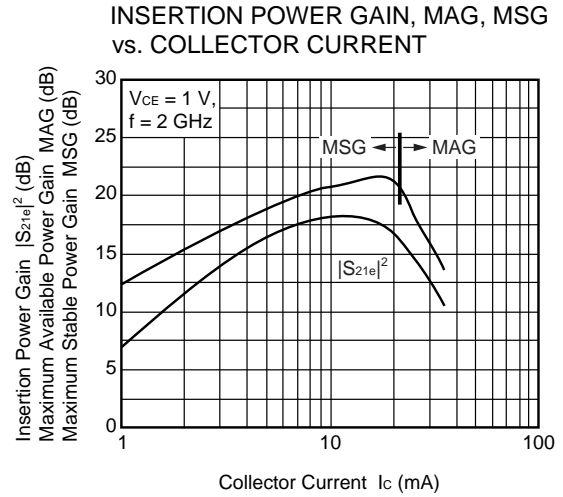
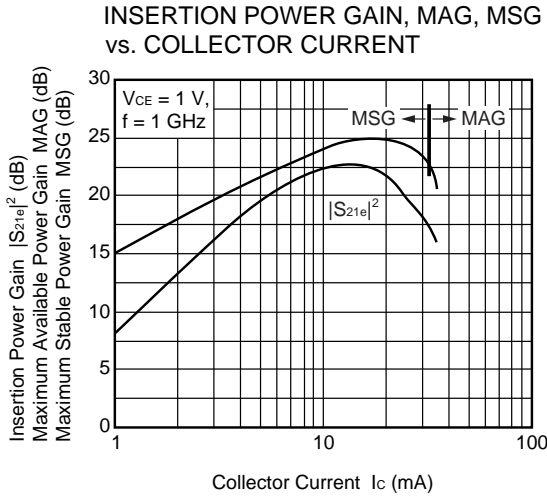
INSERTION POWER GAIN, MAG, MSG vs. FREQUENCY



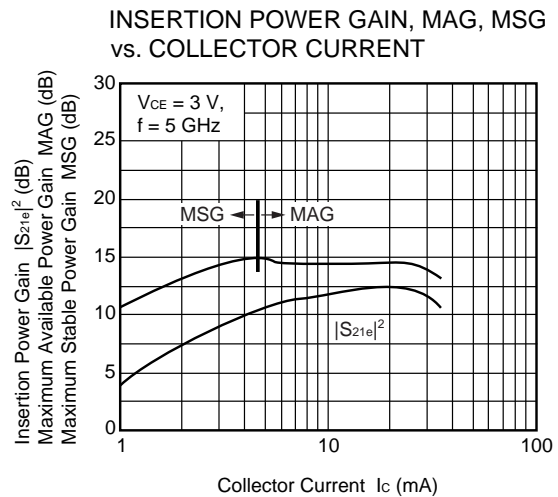
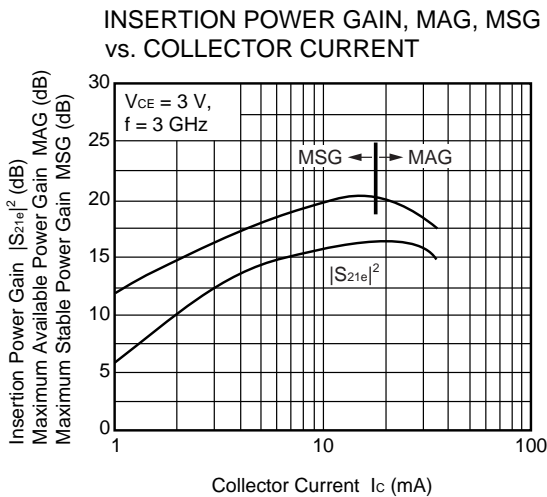
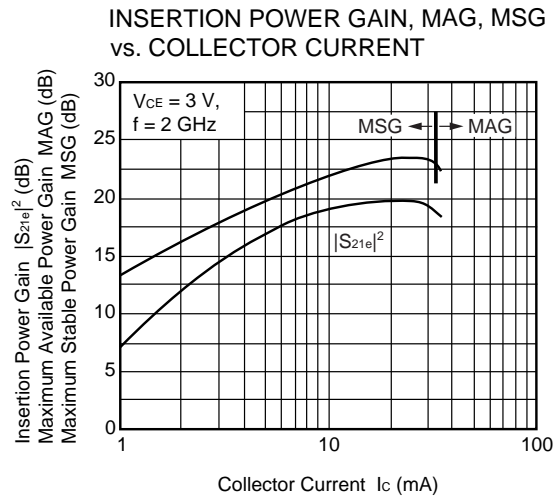
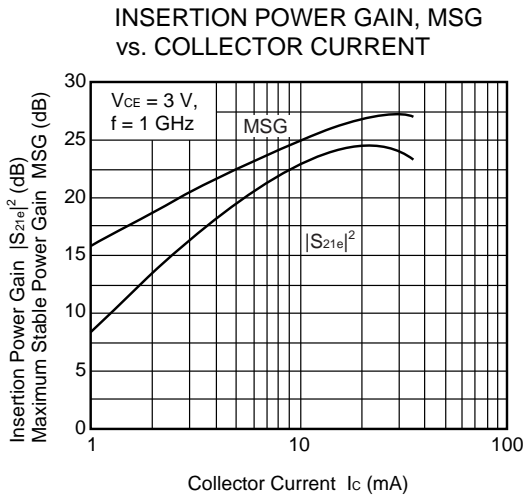
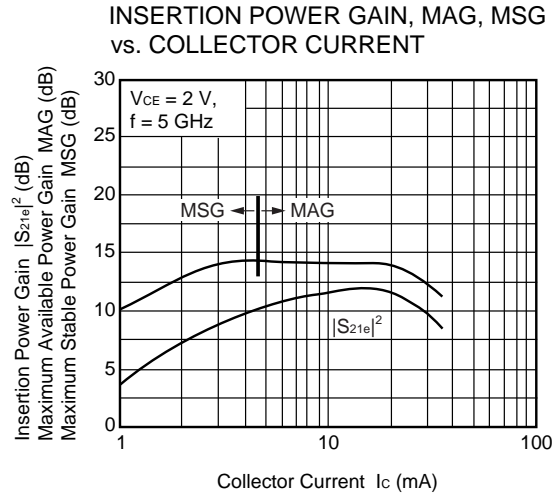
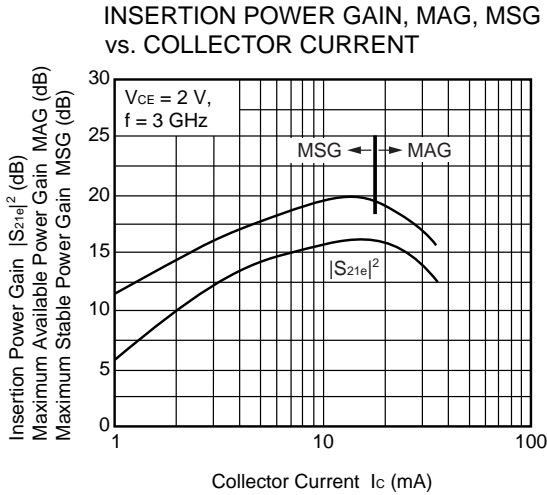
INSERTION POWER GAIN, MAG, MSG vs. FREQUENCY



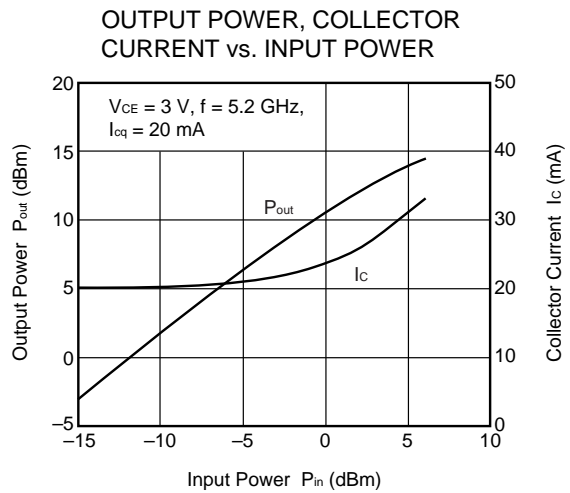
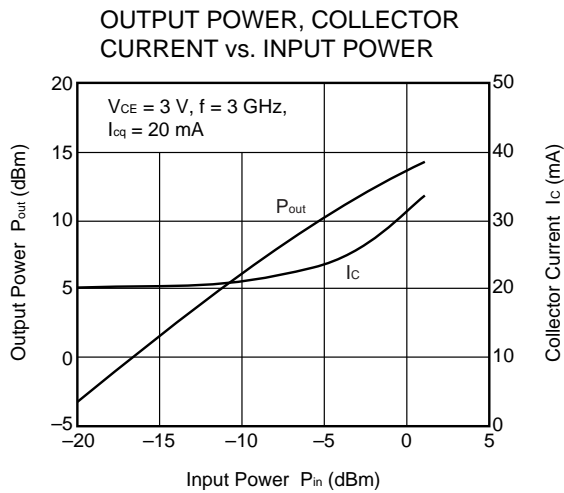
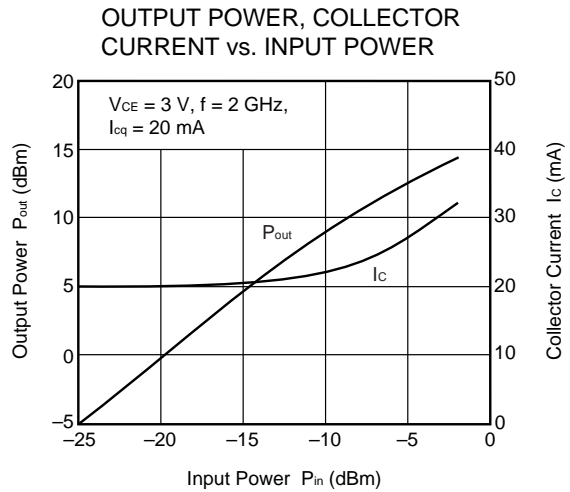
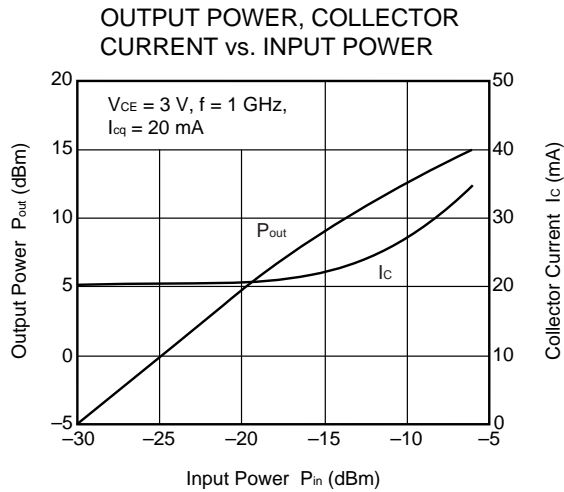
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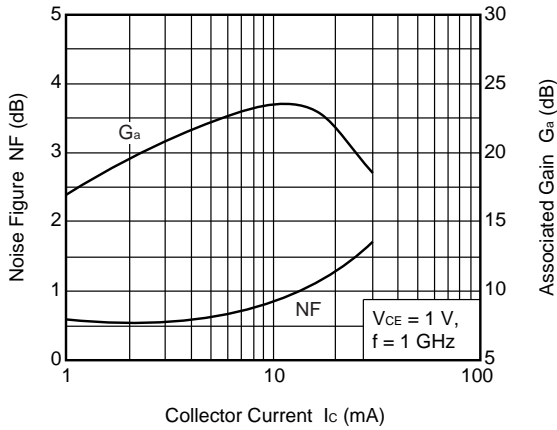


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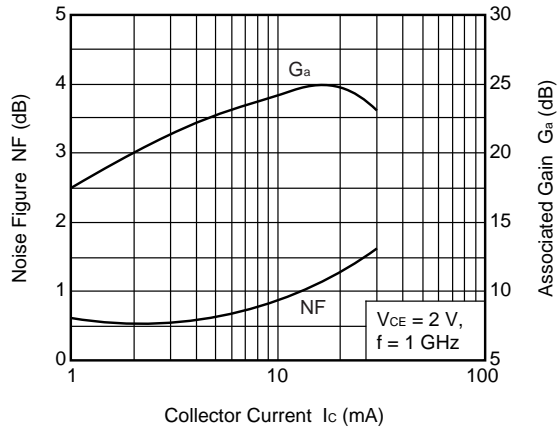


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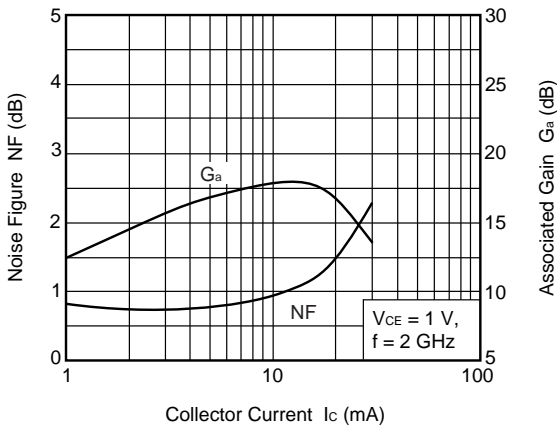
NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



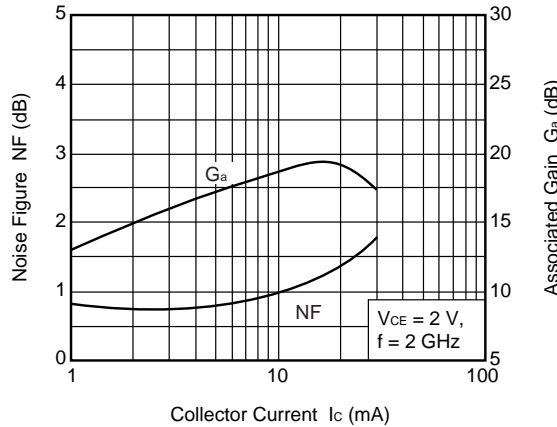
NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



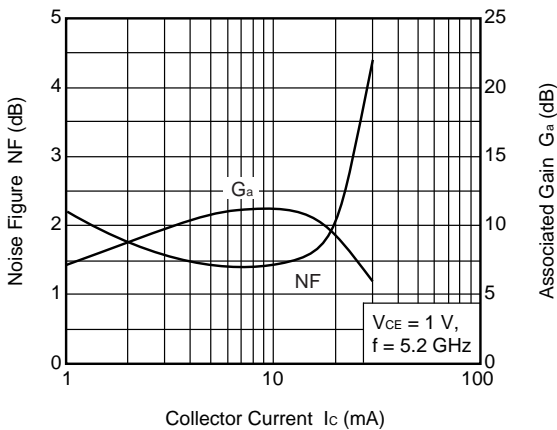
NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



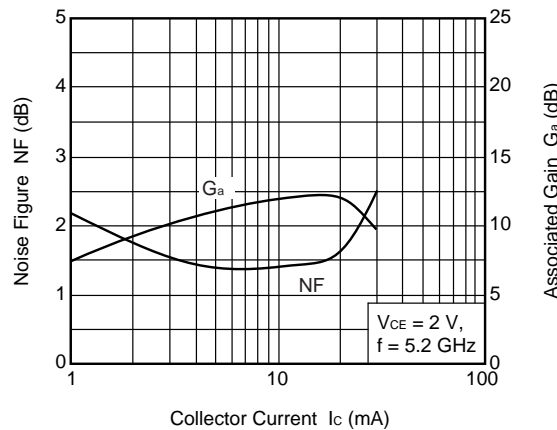
NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



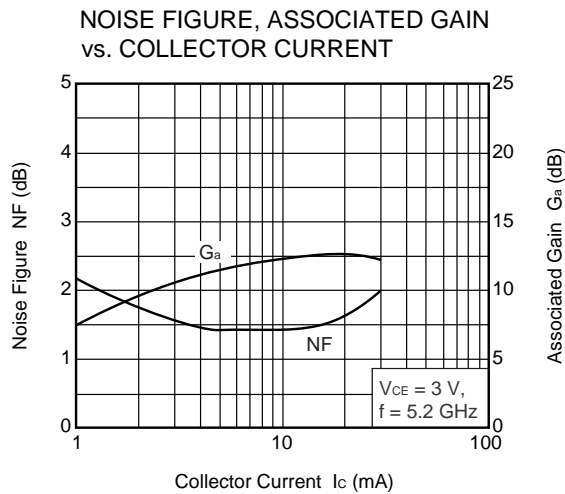
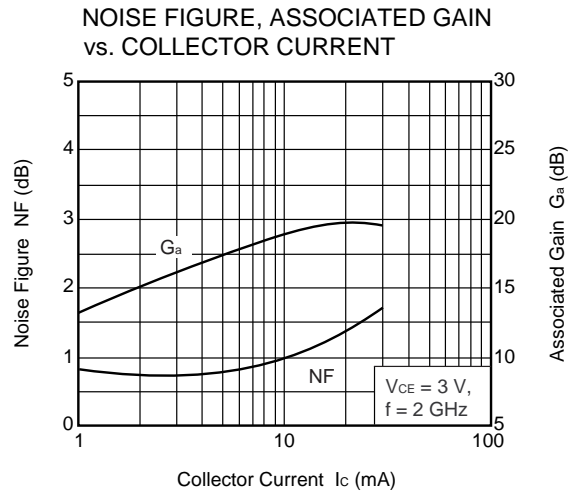
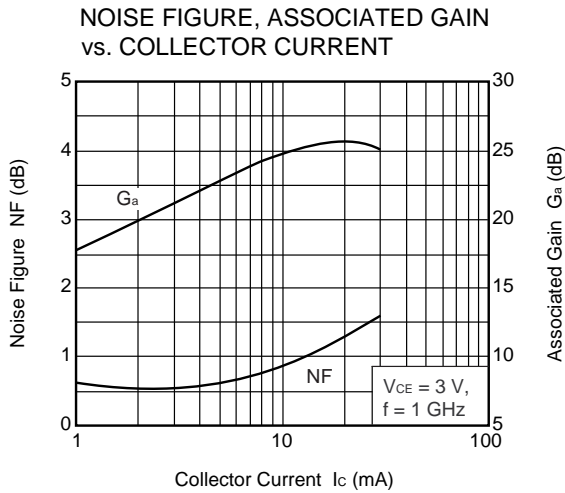
NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



Remark The graphs indicate nominal characteristics.



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<R> **S-PARAMETERS**

S-parameters and noise parameters are provided on our Web site in a format (S2P) that enables the direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.

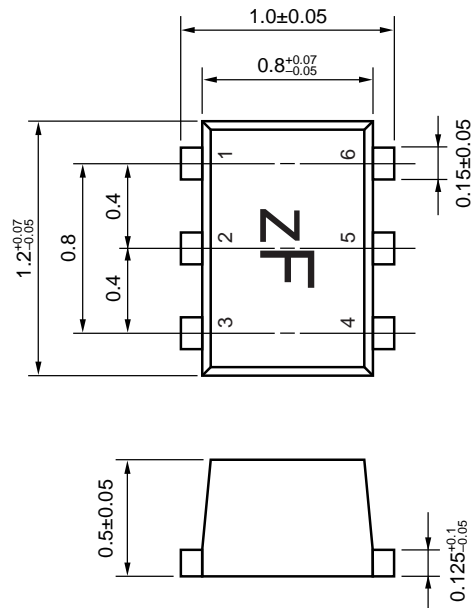
Click here to download S-parameters.

[RF and Microwave] → [Device Parameters]

URL <http://www.necel.com/microwave/en/>

PACKAGE DIMENSIONS

6-PIN LEAD-LESS MINIMOLD (M16, 1208 PKG) (UNIT: mm)



PIN CONNECTIONS

1. Collector
2. Emitter
3. Emitter
4. Base
5. Emitter
6. Emitter

Caution All four Emitter-pins should be connected to PWB in order to obtain better Electrical performance and heat sinking.

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